BTA416Y-600B



3Q Hi-Com Triac Rev. 3 — 27 June 2011

Product data sheet

1. **Product profile**

1.1 General description

Planar passivated high commutation three quadrant triac in a SOT78D (TO-220AB) plastic package intended for use in circuits where high static and dynamic dV/dt and high dl/dt can occur. This "series B" triac will commutate the full RMS current at the maximum rated junction temperature without the aid of a snubber. This device has high junction temperature operating capability and an internally isolated mounting base.

1.2 Features and benefits

- 2500 V RMS isolation voltage capability
- 3Q technology for improved noise immunity
- High commutation capability with maximum false trigger immunity
- High immunity to false turn-on by dV/dt
- High junction temperature operating capability

- High surge capability
- High voltage capability
- Internally insulated package
- Internally isolated mounting base
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only

1.3 Applications

- Electronic thermostats (heating and cooling)
- High power motor controls e.g. vacuum cleaners
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	600	V
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; see Figure 4; see Figure 5	-	-	160	Α
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 108 ^{\circ}\text{C}$; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	-	16	Α



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 7}}{\text{Figure 7}}$	2	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{\text{Figure 7}}$	2	-	50	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 7}}{\text{I}}$	2	-	50	mA

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		N. 1
2	T2	main terminal 2	mb	T2 T1
3	G	gate		sym051
mb	n.c.	mounting base; isolated	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
			SOT78D (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA416Y-600B	TO-220AB	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-220	SOT78D

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		,			
Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 108 \text{ °C}$; see <u>Figure 1</u> ; see <u>Figure 2</u> ; see <u>Figure 3</u>	-	16	Α
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	160	Α
		full sine wave; $T_{j(init)} = 25$ °C; $t_p = 16.7$ ms	-	176	Α
I ² t	I ² t for fusing	t _p = 10 ms; sine-wave pulse	-	128	A ² s
dI _T /dt	rate of rise of on-state current	$I_T = 20 \text{ A}$; $I_G = 0.2 \text{ A}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
I_{GM}	peak gate current		-	4	Α
P_{GM}	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	1	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	150	°C

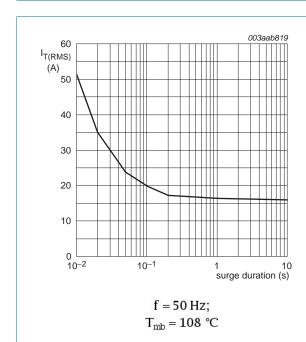


Fig 1. RMS on-state current as a function of surge duration; maximum values

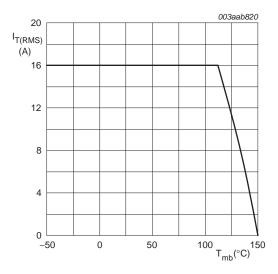


Fig 2. RMS on-state current as a function of mounting base temperature; maximum values

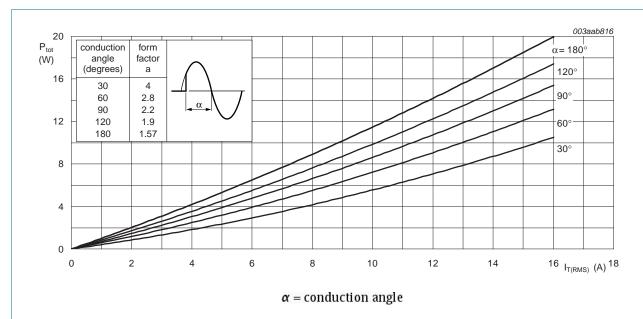


Fig 3. Total power dissipation as a function of RMS on-state current; maximum values

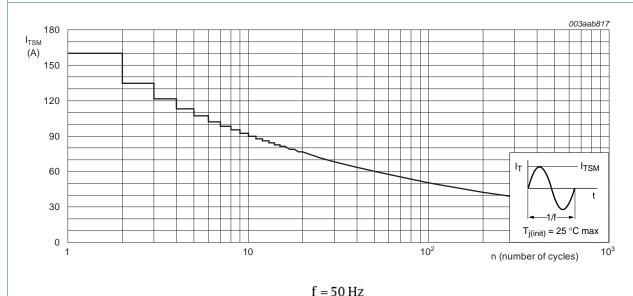
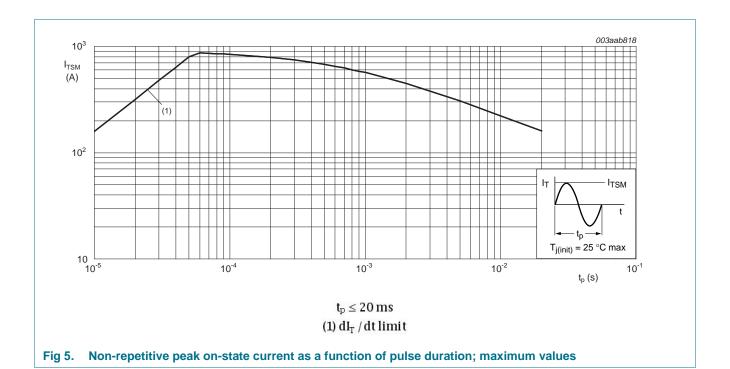


Fig 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; see Figure 6	-	-	1.9	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

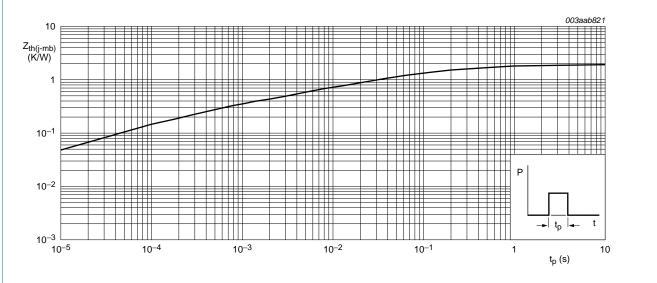


Fig 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Isolation characteristics

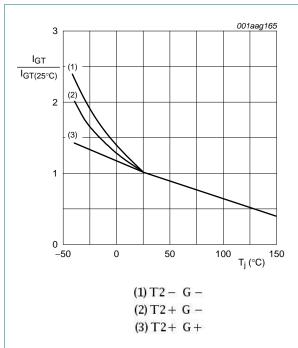
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	from all terminals to external heatsink; sinusoidal waveform; clean and dust free ; 50 Hz \leq f \leq 60 Hz; RH \leq 65 %; T _{mb} = 25 °C	-	-	2500	V
C _{isol}	isolation capacitance	from main terminal 2 to external heatsink; $f = 1 \text{ MHz}$; $T_{mb} = 25 \text{ °C}$	-	10	-	pF

7. Characteristics

Table 7. Characteristics

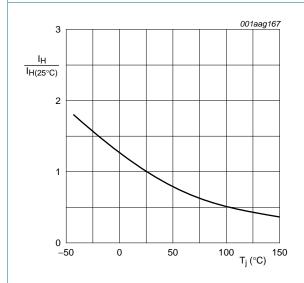
Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+; T_j = 25 \text{ °C;}$ see Figure 7	2	-	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G-; } T_j = 25 \text{ °C; } $ see Figure 7	2	-	50	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2\text{- }G\text{-; } T_j = 25 ^{\circ}\text{C;}$ see Figure 7	2	-	50	mA
l _L	latching current	$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2+ G+; T_j = 25 \text{ °C;}$ see Figure 8	-	-	60	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2 + G-; T_j = 25 \text{ °C;}$ see Figure 8	-	-	90	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2\text{- }G\text{-}; T_j = 25 \text{ °C;}$ see Figure 8	-	-	60	mA
I _H	holding current	$V_D = 12 \text{ V}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{}$	-	-	60	mΑ
V _T	on-state voltage	I _T = 20 A; T _j = 25 °C; see <u>Figure 10</u>	-	1.2	1.5	V
V _{GT} gate	gate trigger voltage	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T_j = 25 \text{ °C;}$ see Figure 11	-	0.7	1.5	V
		V _D = 400 V; I _T = 0.1 A; T _j = 150 °C	0.25	0.4	-	V
I _D	off-state current	$V_D = 600 \text{ V}; T_j = 125 ^{\circ}\text{C}$	-	0.1	0.5	mA
		V _D = 600 V; T _j = 150 °C	-	0.4	2	mA
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; exponential waveform; gate open circuit	1000	-	-	V/µs
		$V_{DM} = 402 \text{ V}$; $T_j = 150 \text{ °C}$; exponential waveform; gate open circuit	600	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}$; $T_j = 125 \text{ °C}$; $I_{T(RMS)} = 16 \text{ A}$; $dV_{com}/dt = 20 \text{ V/}\mu\text{s}$; (without snubber condition); gate open circuit	15	-	-	A/ms
		$V_D = 400 \text{ V}; T_j = 150 \text{ °C}; I_{T(RMS)} = 16 \text{ A};$ $dV_{com}/dt = 20 \text{ V/}\mu\text{s};$ (without snubber condition); gate open circuit	6	-	-	A/ms
t _{gt}	gate-controlled turn-on time	$I_{TM} = 20 \text{ A}; V_D = 600 \text{ V}; I_G = 100 \text{ mA};$ $dI_G/dt = 5 \text{ A}/\mu\text{s}$	-	2	-	μs

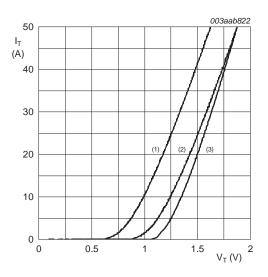


3 IL IL(25°C) 2 1 0 -50 0 50 100 T_j (°C)

Fig 7. Normalized gate trigger current as a function of junction temperature

Fig 8. Normalized latching current as a function of junction temperature

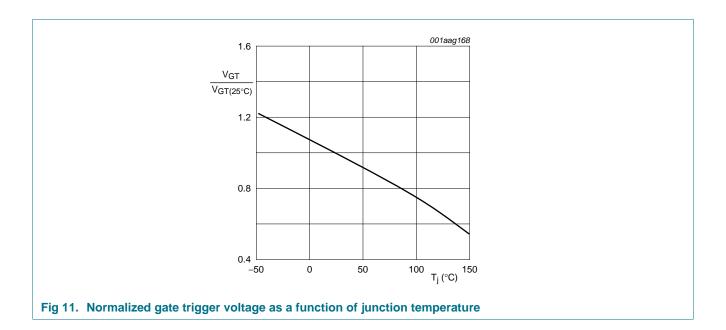




 $V_o=1.086~V$ $R_s=0.017~\Omega$ (1) $T_j=150~^{\circ}C;$ typical values (2) $T_j=150~^{\circ}C;$ maximum values (3) $T_j=25~^{\circ}C;$ maximum values

Fig 9. Normalized holding current as a function of junction temperature

Fig 10. On-state current as a function of on-state voltage



Product data sheet

8. Package outline

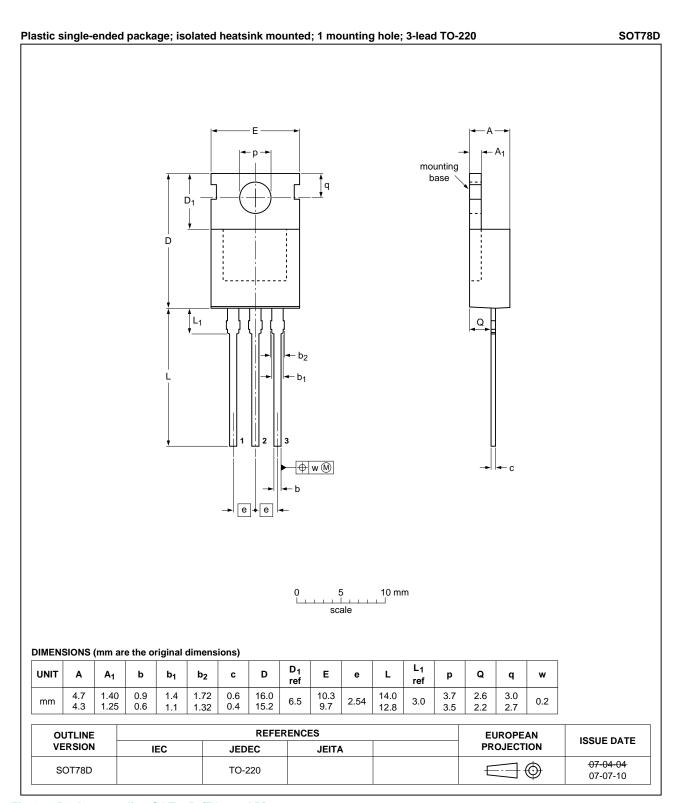


Fig 12. Package outline SOT78D (TO-220AB)

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA416Y-600B v.3	20110627	Product data sheet	-	BTA412Y_SER_B_C v.2
Modifications: • Type number BTA416Y-600B separated from data sheet BTA412Y_SER_B_C v.2.				A412Y_SER_B_C v.2.
	 Various change 	s to content.		
BTA412Y_SER_B_C v.2	20080311	Product data sheet	-	-

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Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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12. Contents

1	Product profile
1.1	General description1
1.2	Features and benefits1
1.3	Applications1
1.4	Quick reference data1
2	Pinning information2
3	Ordering information2
4	Limiting values3
5	Thermal characteristics6
6	Isolation characteristics
7	Characteristics7
8	Package outline
9	Revision history11
10	Legal information12
10.1	Data sheet status
10.2	Definitions12
10.3	Disclaimers
10.4	Trademarks13
11	Contact information13

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